

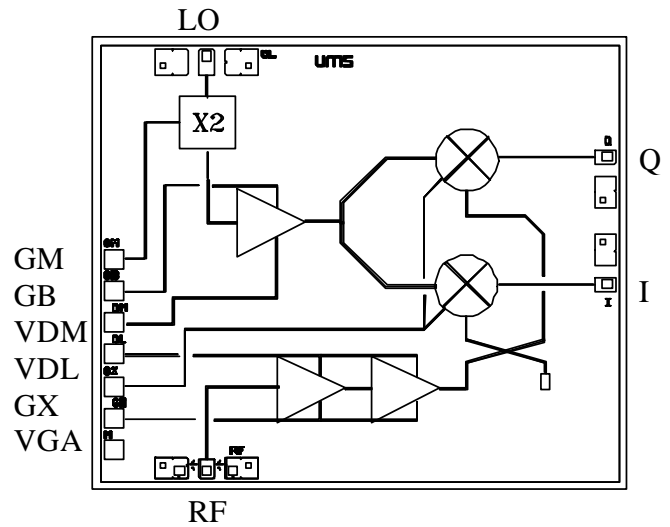
20-24GHz Integrated Down Converter

GaAs Monolithic Microwave IC

Description

The CHR2293 is a multifunction chip which integrates a LO X2 multiplier, a balanced cold FET mixer, and a RF LNA. It is designed for a wide range of applications, typically commercial communication systems. The backside of the chip is both RF and DC grounds. This helps simplify the assembly process.

The circuit is manufactured with a PM-HEMT process, 0.25 μ m gate length, via holes through the substrate, air bridges and electron beam gate lithography. It is available in chip form.



Main Features

- Broadband performances : 20-24GHz
- 11 dB conversion gain
- 4dB noise figure
- 10dBm LO input power
- -8dBm RF input power (1dB gain comp.)
- Low DC power consumption, 130mA@3.5V
- Chip size : 2.49 X 1.97 X 0.10 mm

Main Characteristics

Tamb. = 25°C

	Parameter	Min	Typ	Max	Unit
F _{RF}	RF frequency range	20		24	GHz
F _{LO}	LO frequency range	9.25		12.75	GHz
F _{IF}	IF frequency range	0.25		1.5	GHz
G _c	Conversion gain		+11		dB

ESD Protection : Electrostatic discharge sensitive device. Observe handling precautions !

Electrical Characteristics for Broadband Operation

Tamb = +25°C, Vdm = Vdl = 3.5V, Vgm=-0.9V, Vgb=-0.7V, Vgx=-0.8V, Vga=-0.55V

Symbol	Parameter	Min	Typ	Max	Unit
F _{RF}	RF frequency range	20		24	GHz
F _{LO}	LO frequency range	9.25		12.75	GHz
F _{IF}	IF frequency range	0.25		1.5	GHz
G _c	Conversion gain (1)		+11		dB
NF	Noise Figure (1)		4		dB
P _{LO}	LO Input power		+10		dBm
Img Sup	Image Suppression (2)	13	17		dBc
P1dB	Input power at 1dB gain compression		-8		dBm
LO VSWR	Input LO VSWR (1)		2.0:1		
RF VSWR	Input RF VSWR (1)		2.0:1		
I _d	Bias current (3)		130		mA

(1) On Wafer measurements

(2) With external I/ Q combiner

(3) Current source biasing network is recommended. Optimum performances for I_{dm}= 50mA and I_{dl}= 80mA

Absolute Maximum Ratings

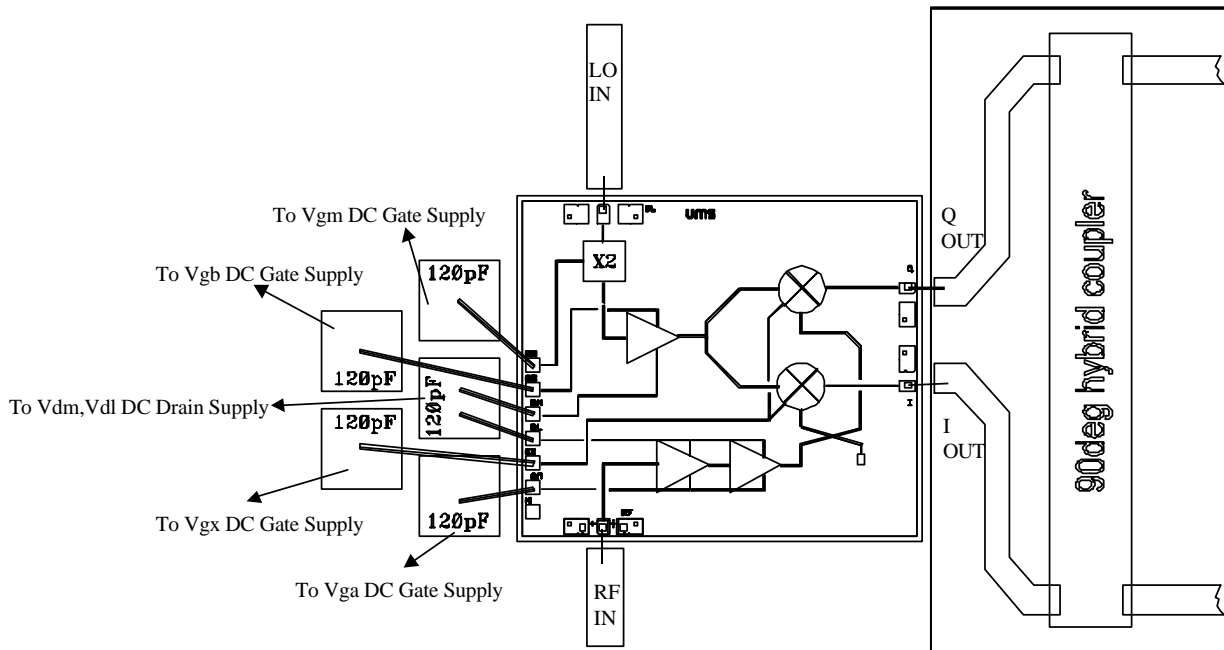
Tamb. = 25°C (1)

Symbol	Parameter	Values	Unit
V _d	Drain bias voltage	4.0	V
I _d	Drain bias current	200	mA
V _g	Gate bias voltage	-2.0 to +0.4	V
P _{in}	Maximum peak input power overdrive (2)	+15	dBm
T _a	Operating temperature range	-40 to +85	°C
T _{stg}	Storage temperature range	-55 to +155	°C

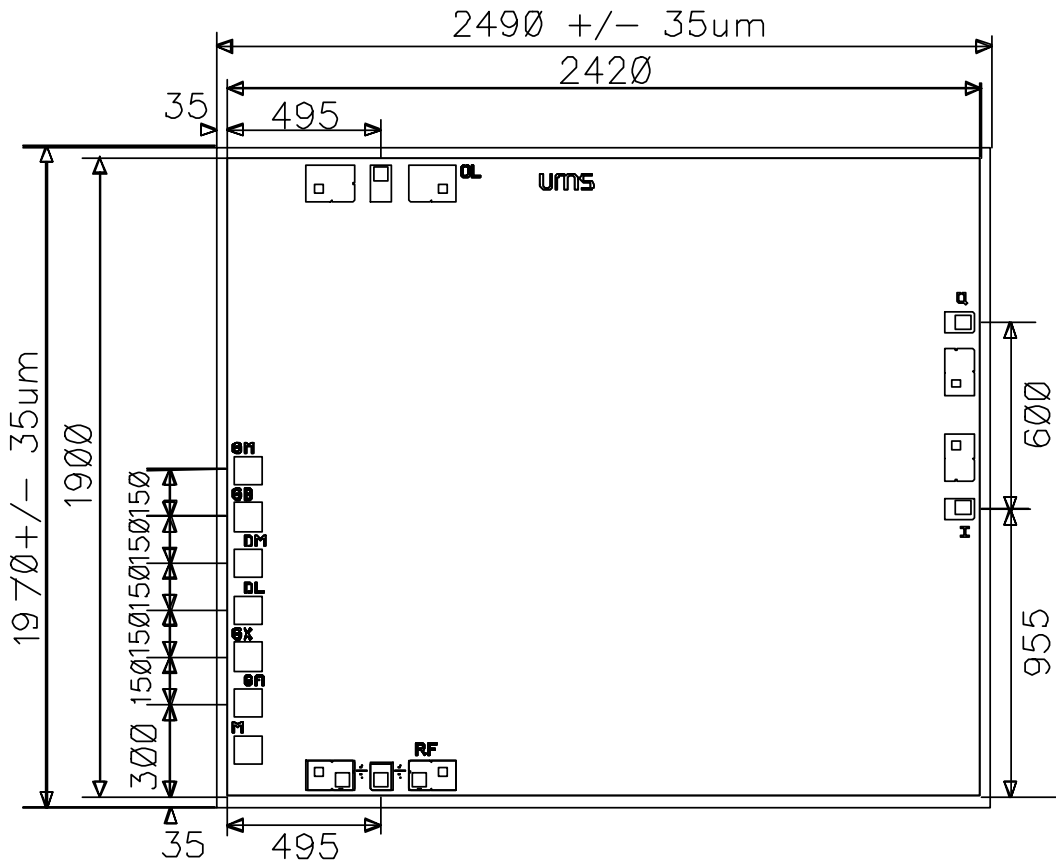
(1) Operation of this device above anyone of these parameters may cause permanent damage.

(2) Duration < 1s.

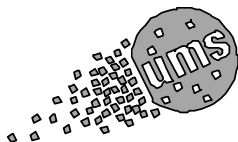
Chip Assembly and Mechanical Data



Note : Supply feed should be capacitively bypassed. 25µm diameter gold wire is recommended



Bonding pad positions
(Chip thickness : 100µm. All dimensions are in micrometers)



Ordering Information

Chip form : CHR2293-99F/00

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